S8550

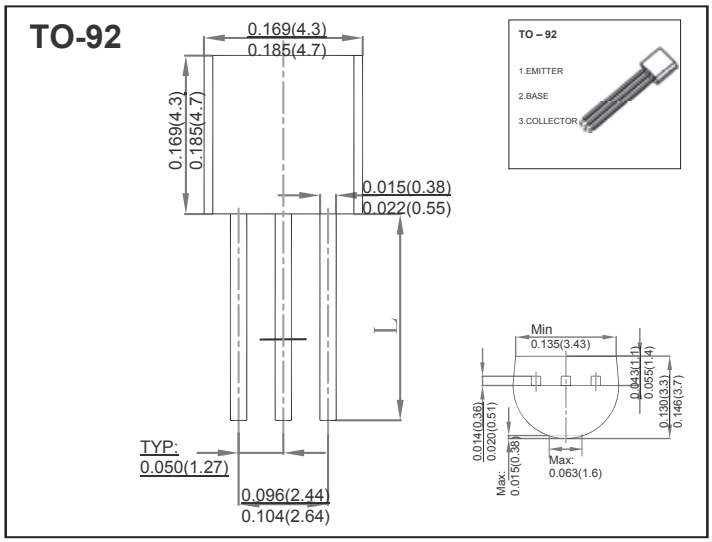
TO-92 Plastic-Encapsulate Transistors

FEATURE

- Excellent h_{FE} Linearity

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

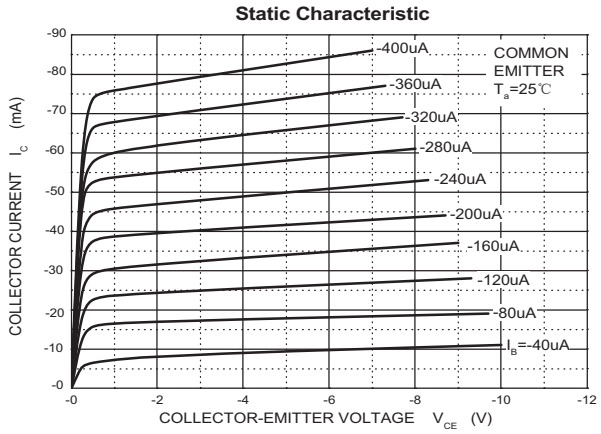
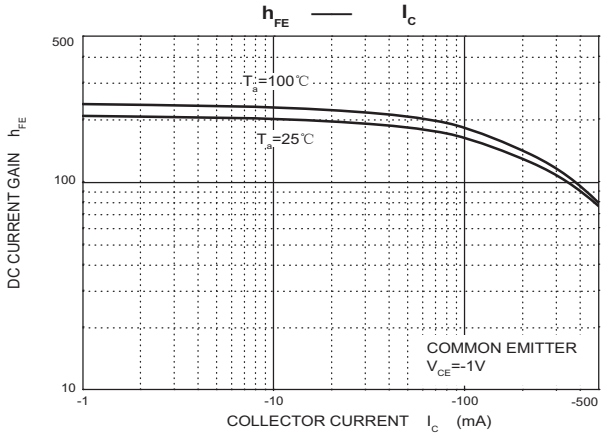
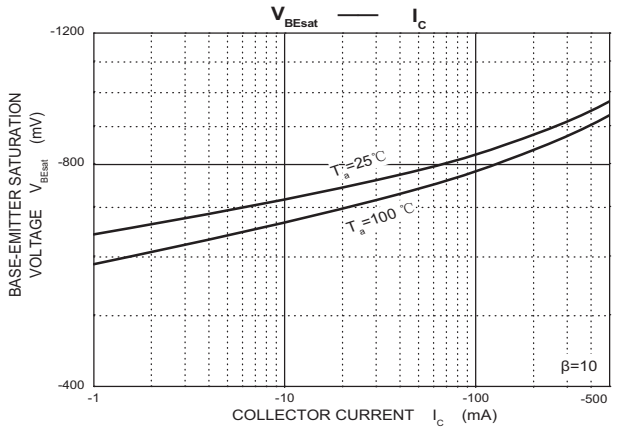
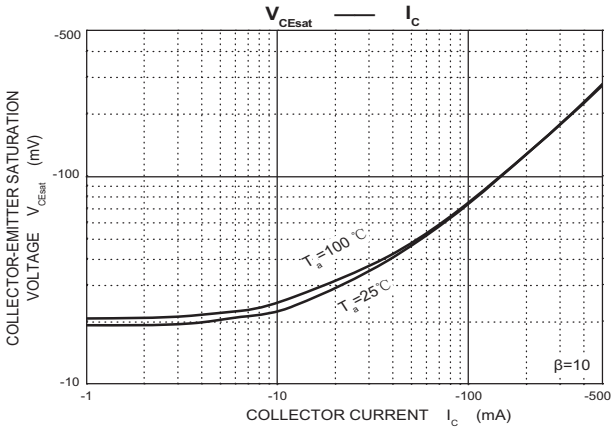
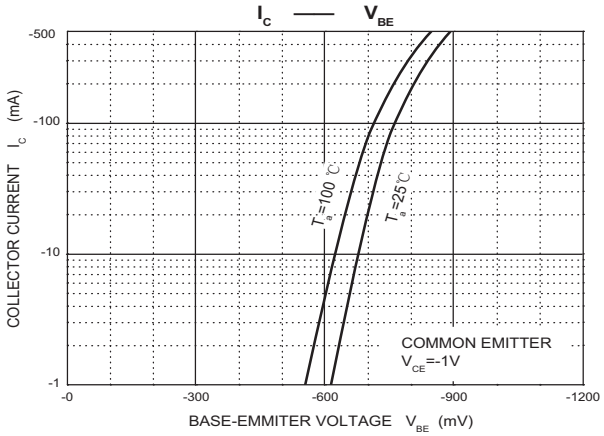
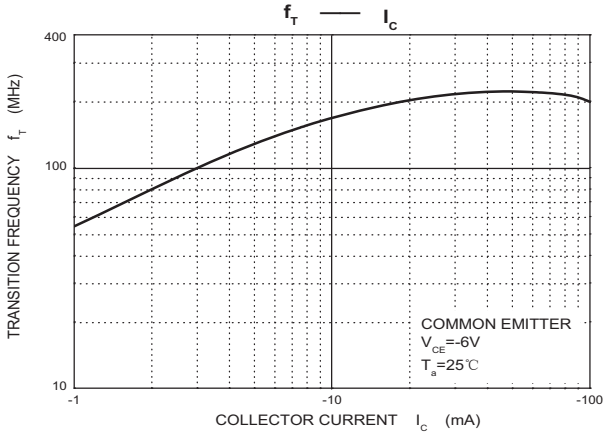
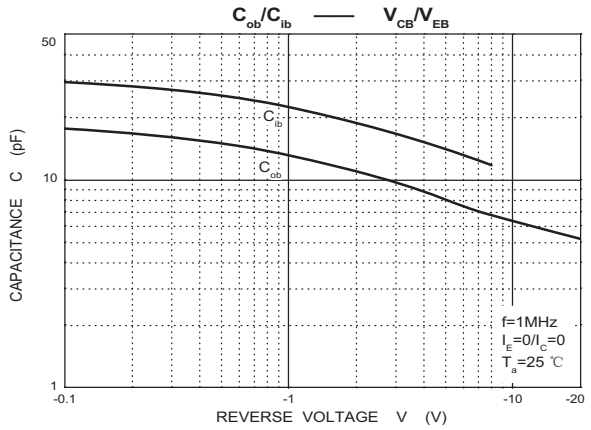
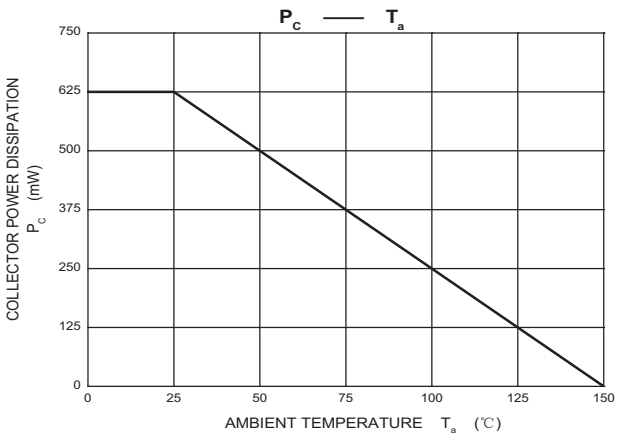
@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.5	A
P_D	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	200	℃ /W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55～+150	℃

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -100uA, I_E=0	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -1mA, I_B=0	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -100uA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}= -40V, I_E=0			-0.1	uA
Collector cut-off current	I_{CEO}	V_{CE}= -20V, I_B=0			-0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= - 3V, I_C=0			-0.1	uA
DC current gain	$h_{FE(1)}$	V_{CE}= -1V, I_C= -50mA	85		400	
	$h_{FE(2)}$	V_{CE}= -1V, IC= -500mA	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA			-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-500mA, I_B=-50mA			-1.2	V
Transition frequency	f_T	V_{CE}=- 6V, I_C=-20mA, f =30MHz	150			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	B	C	D	D3
Range	85-160	120-200	160- 300	300- 400

RATINGS AND CHARACTERISTIC CURVES

Typical Characterisitics